

# FDS8670

## 30V N-Channel PowerTrench® MOSFET

### General Description

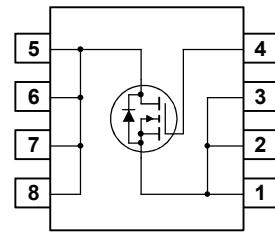
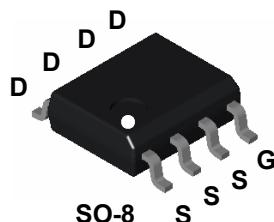
This device has been designed specifically to improve the efficiency of DC-DC converters. Using new techniques in MOSFET construction, the various components of gate charge and capacitance have been optimized to reduce switching losses. Low gate resistance and very low Miller charge enable excellent performance with both adaptive and fixed dead time gate drive circuits. Very low  $R_{ds(on)}$  has been maintained to provide an extremely versatile device.

### Applications

- High Efficiency DC-DC Converters:
  - Notebook Vcore Power Supply
  - Telecom Brick Synchronous Rectifier
  - Multi purpose Point Of Load

### Features

- 21 A, 30 V      Max  $R_{ds(on)}$  = 3.7 mΩ @  $V_{GS} = 10$  V  
Max  $R_{ds(on)}$  = 5.0 mΩ @  $V_{GS} = 4.5$  V
- High performance trench technology for extremely low  $R_{ds(on)}$  and gate charge
- Minimal  $Q_{gd}$  (5.5 nC typical)
- 100%  $R_G$  tested (0.9 Ω typical)
- 100% UIL tested
- RoHS Compliant



### Absolute Maximum Ratings

$T_A=25^\circ\text{C}$  unless otherwise noted

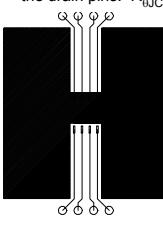
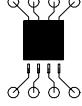
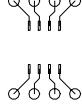
Symbol	Parameter	Ratings	Units
$V_{DSS}$	Drain-Source Voltage	30	V
$V_{GSS}$	Gate-Source Voltage	$\pm 20$	V
$I_D$	Drain Current – Continuous (Note 1a)	21	A
	– Pulsed	105	
$P_D$	Power Dissipation (Note 1a)	2.5	W
	(Note 1b)	1.2	
	(Note 1c)	1	
$E_{AS}$	Single Pulse Avalanche Energy (Note 3)	433	mJ
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range	–55 to +150	°C

### Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1a)	50	°C/W
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case (Note 1)	25	

### Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
FDS8670	FDS8670	13"	12mm	2500 units

Electrical Characteristics							
$T_A = 25^\circ\text{C}$ unless otherwise noted							
Symbol	Parameter	Test Conditions	Min	Typ	Max	Units	
<b>Off Characteristics</b>							
$\text{BV}_{\text{DSS}}$	Drain-Source Breakdown Voltage	$V_{\text{GS}} = 0 \text{ V}$ , $I_D = 250 \mu\text{A}$	30			V	
$\Delta \text{BV}_{\text{DSS}}$ $\Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250 \mu\text{A}$ , Referenced to $25^\circ\text{C}$		39		$\text{mV/}^\circ\text{C}$	
$I_{\text{DS}}^{\text{SS}}$	Zero Gate Voltage Drain Current	$V_{\text{DS}} = 24 \text{ V}$ , $V_{\text{GS}} = 0 \text{ V}$			1	$\mu\text{A}$	
$I_{\text{GSS}}$	Gate-Body Leakage	$V_{\text{GS}} = \pm 20 \text{ V}$ , $V_{\text{DS}} = 0 \text{ V}$			$\pm 100$	nA	
<b>On Characteristics</b> (Note 2)							
$V_{\text{GS}(\text{th})}$	Gate Threshold Voltage	$V_{\text{DS}} = V_{\text{GS}}$ , $I_D = 250 \mu\text{A}$	1	1.4	3	V	
$\Delta V_{\text{GS}(\text{th})}$ $\Delta T_J$	Gate Threshold Voltage Temperature Coefficient	$I_D = 250 \mu\text{A}$ , Referenced to $25^\circ\text{C}$		-5		$\text{mV/}^\circ\text{C}$	
$R_{\text{DS}(\text{on})}$	Static Drain-Source On-Resistance	$V_{\text{GS}} = 10 \text{ V}$ , $I_D = 21 \text{ A}$ $V_{\text{GS}} = 4.5 \text{ V}$ , $I_D = 18 \text{ A}$ $V_{\text{GS}} = 10 \text{ V}$ , $I_D = 21 \text{ A}$ , $T_J = 125^\circ\text{C}$		3.3 4.2 4.4	3.7 5.0 5.5	$\text{m}\Omega$	
$g_{\text{FS}}$	Forward Transconductance	$V_{\text{DS}} = 10 \text{ V}$ , $I_D = 21 \text{ A}$		118		S	
<b>Dynamic Characteristics</b>							
$C_{\text{iss}}$	Input Capacitance	$V_{\text{DS}} = 15 \text{ V}$ , $V_{\text{GS}} = 0 \text{ V}$ , $f = 1.0 \text{ MHz}$		4040		pF	
$C_{\text{oss}}$	Output Capacitance			1730		pF	
$C_{\text{rss}}$	Reverse Transfer Capacitance			160		pF	
$R_G$	Gate Resistance	$f = 1.0 \text{ MHz}$	0.2	0.9	1.5	$\Omega$	
<b>Switching Characteristics</b> (Note 2)							
$t_{\text{d}(\text{on})}$	Turn-On Delay Time	$V_{\text{DD}} = 15 \text{ V}$ , $I_D = 1 \text{ A}$ , $V_{\text{GS}} = 10 \text{ V}$ , $R_{\text{GEN}} = 6 \Omega$		12	21	ns	
$t_r$	Turn-On Rise Time			11	20	ns	
$t_{\text{d}(\text{off})}$	Turn-Off Delay Time			56	90	ns	
$t_f$	Turn-Off Fall Time			68	108	ns	
$Q_{\text{g}(\text{TOT})}$	Total Gate Charge at $V_{\text{GS}} = 10 \text{ V}$	$V_{\text{DD}} = 15 \text{ V}$ , $I_D = 21 \text{ A}$		58.5	82	nC	
$Q_{\text{g}(\text{TOT})}$	Total Gate Charge at $V_{\text{GS}} = 5 \text{ V}$			30	42	nC	
$Q_{\text{gs}}$	Gate-Source Charge			9.5		nC	
$Q_{\text{gd}}$	Gate-Drain Charge			5.5		nC	
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>							
$V_{\text{SD}}$	Drain-Source Diode Forward Voltage	$V_{\text{GS}} = 0 \text{ V}$ , $I_S = 2.1 \text{ A}$ (Note 2)		0.7	1.2	V	
$t_{\text{rr}}$	Diode Reverse Recovery Time	$I_F = 21 \text{ A}$ , $dI_F/dt = 100 \text{ A}/\mu\text{s}$		51		ns	
$I_{\text{RM}}$	Diode Reverse Recovery Current			1.5		A	
$Q_{\text{rr}}$	Diode Reverse Recovery Charge			37		nC	
<b>Notes:</b>							
1. $R_{\text{QJA}}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\text{QJC}}$ is guaranteed by design while $R_{\text{QCA}}$ is determined by the user's board design.							
 a) 50°/W when mounted on a 1 in² pad of 2 oz copper							
 b) 105°/W when mounted on a .04 in² pad of 2 oz copper							
 c) 125°/W when mounted on a minimum pad.							
Scale 1 : 1 on letter size paper							
2. Pulse Test: Pulse Width < 300 μs, Duty Cycle < 2.0%							
3. Starting $T_J = 25^\circ\text{C}$ , $L = 3 \text{ mH}$ , $I_{AS} = 17 \text{ A}$ , $V_{DD} = 30 \text{ V}$ , $V_{GS} = 10 \text{ V}$							

## Typical Characteristics

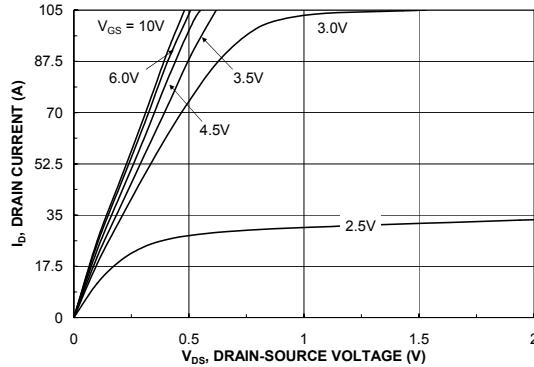


Figure 1. On-Region Characteristics.

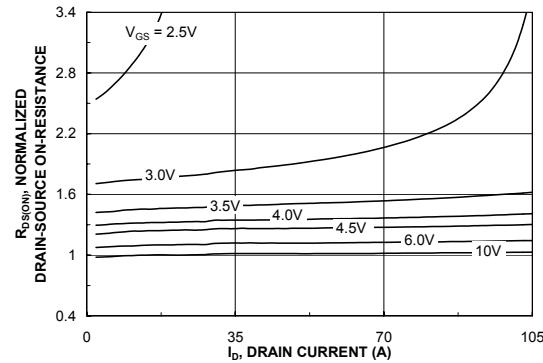


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

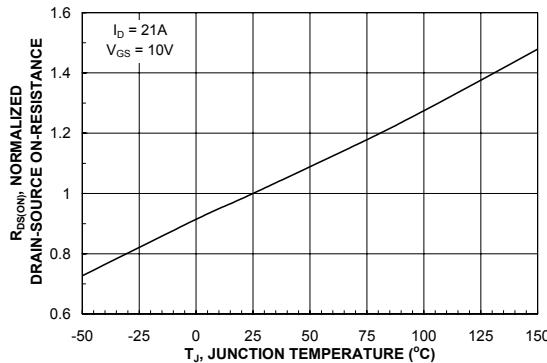


Figure 3. On-Resistance Variation with Temperature.

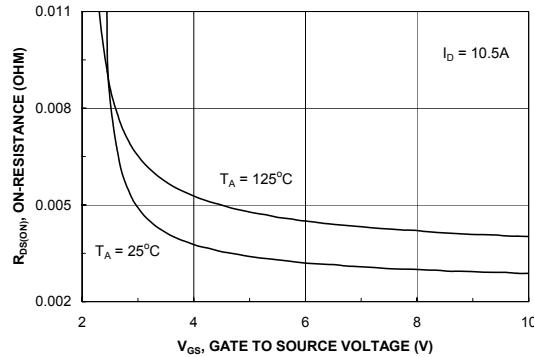


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

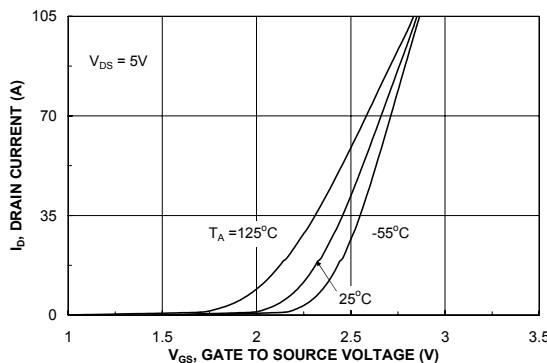


Figure 5. Transfer Characteristics.

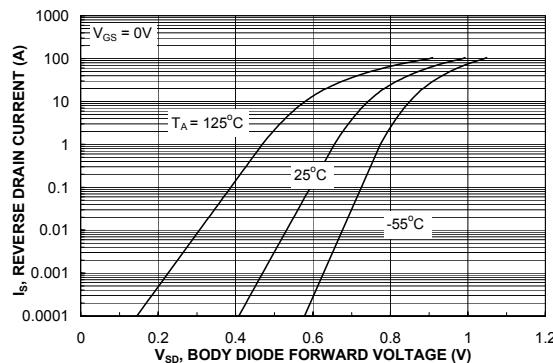


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

### Typical Characteristics (continued)

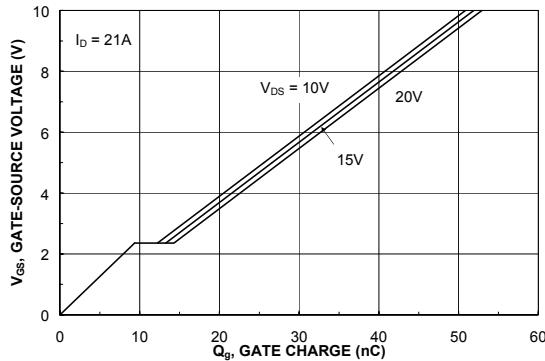


Figure 7. Gate Charge Characteristics.

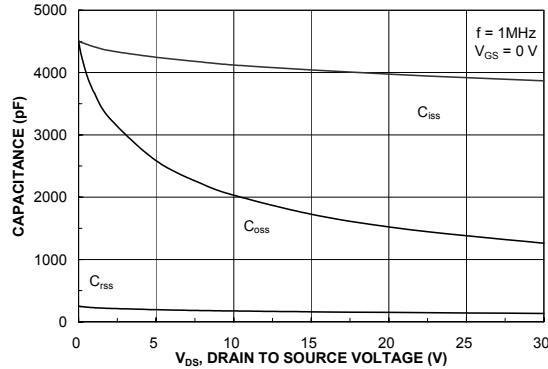


Figure 8. Capacitance Characteristics.

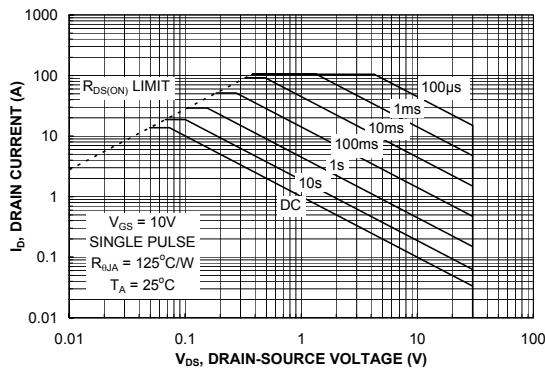


Figure 9. Maximum Safe Operating Area.

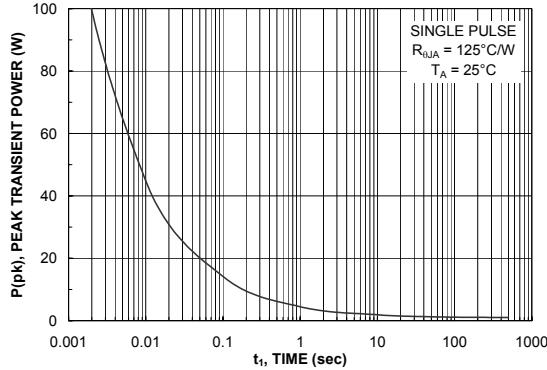


Figure 10. Single Pulse Maximum Power Dissipation.

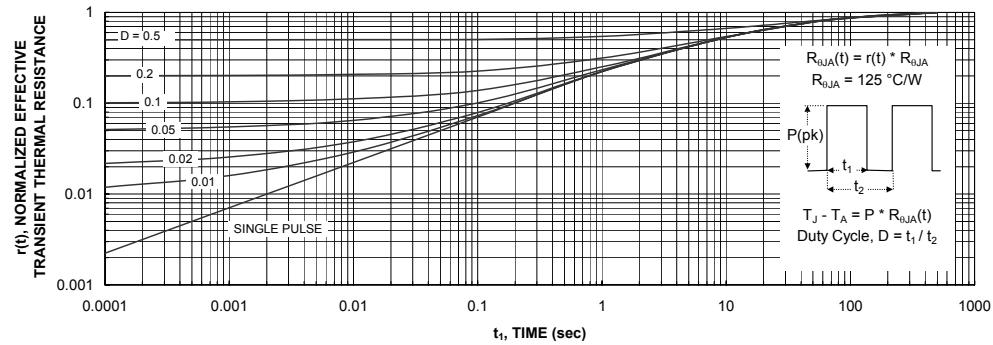


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1c.  
Transient thermal response will change depending on the circuit board design.



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